

ABSTRACT OF THE DISCLOSURE

A semiconductor structure with active zones, such as light diodes or photodiodes, including a substrate (SUB) with at least two active zones (AZ1 - AZn), each of which emits or absorbs a radiation of differing wavelength. According to the invention, a multi-wavelength diode may be achieved, in which a first (lower) active zone (AZ1) is grown on a surface of the substrate (SUB), with one or several further active zones (AZ1 - AZn) epitaxially grown one on the other and the active zones (AZ1 - AZn) are serially connected from the lower active zone (AZ1) to an upper active zone (AZn), by means of tunnel diodes (TD1 - TDn), serving as low-impedance resistors.

LAW OFFICES
DENNISON, SCHULTZ & MACDONALD
SUITE 105
1727 KING STREET
ALEXANDRIA, VIRGINIA 22314-2700
703 837-9600